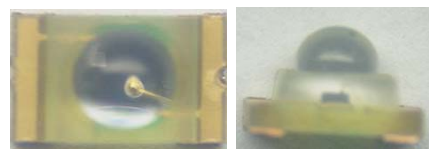


Silicon photo transistor KDT5001A

Description

The KDT5001A is high sensitivity silicon photo transistor which converts light to electrical signal.

This photo transistor is both COB package and easy to mount.



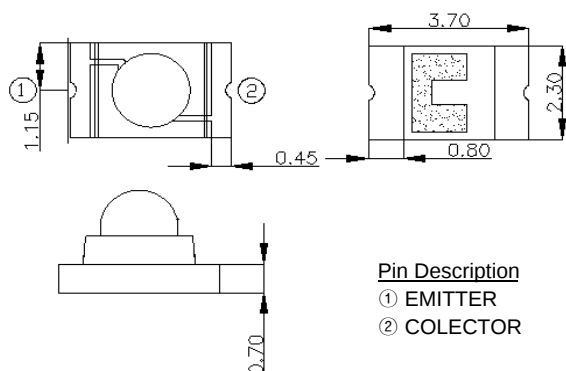
Features

- Highly sensitive photo transistor.
- Chip On Board package.
- High speed response.

Application

- AV Instruments.
- Touch panels for ATM & FA equipments.
- Optical counter

Outline Dimensions



ELECTRO- OPTICAL CHARACTERISTICS

[Ta= 25°C]

Description	Symbol	Condition	Min.	Typ.	Max.	Unit
Dark Current	I_{CEO}	$V_{CE}=10V, E_E=0$	-	-	100	nA
Photo Current	I_{PCE}	$V_{CE}=5V, E_E=0.5mW/cm^2$ $\lambda_{PK}=640nm$	1.2	-	2.4	mA
Spectral Sensitivity	λ		500~1050			nm
Peek wavelength	λ_p	$V_R=0V$		880		nm
Viewing Angle	$2\Theta_{1/2}$		20		40	deg.
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=100\mu A, E_E=0.5mW/cm^2$ $\lambda_{PK}=640nm$	-	-	200	mV